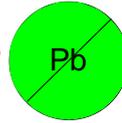


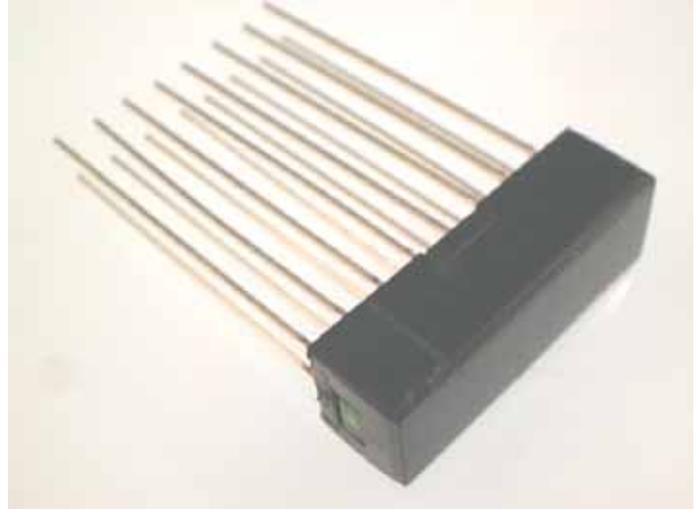
These components are RoHS compliant



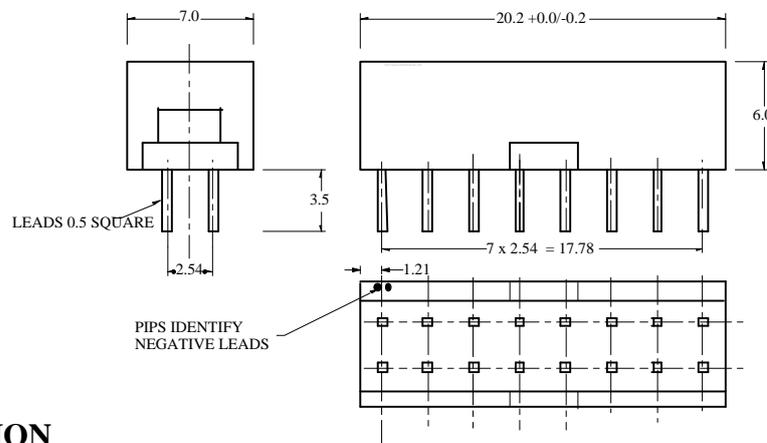
SSA-005-2 Miniature IR Array

SSA-005-2 is an eight element array of silicon phototransistors or gallium arsenide infrared emitters in a polycarbonate housing. It is supplied with either wide angle flat-lensed or narrow angle components. All leads fit an 0.1" inch matrix.

- Very compact 8-element arrays with a double row of leads on an 0.1" matrix.
- End stackable.
- No dust traps to reduce opto performance.
- Smooth black polycarbonate housing transmits infrared but reduces daylight influence.



MECHANICAL



ORDERING INFORMATION

FLAT LENS PHOTOTRANSISTOR=SSA005-2A
DOME LENS PHOTOTRANSISTIR=SSA005-2B
FLAT LENS INFRARED EMITTER=SSA005-2C
DOME LENS INFRARED EMITTER=SSA005-2D

PLEASE NOTE

CAN BE SUPPLIED IN LESS THAN 8 WAY VERSIONS ON REQUEST WITH COUPLED PAIR SPECIFICATION.

BEDFORD OPTO TECHNOLOGY LTD
1,BIGGAR BUSINESS PARK, BIGGAR, LANARKSHIRE,ML12 6NR
Tel: +44 (0) 1899 221221 Fax: +44 (0) 1899 221009
Website: bot.co.uk E-mail: bill@bot.co.uk

ISS C 23.8.07

SOLDERING TEMPERATURE (3secs max 2mm from body) ALL TYPES	260 °C max
--	-------------------

SSA-005-2

INFRARED DIODES

IR-Emitting Diodes in Miniature (T-3/4) Package

PARAMETER	CONDITIONS	SYMBOL	VALUE
Viewing Angle CQY 36N CQY 37N		φ	$\pm 55^\circ$
Peak Wavelength		λ_p	950nm
Power Dissipation		P_v	170mW
Thermal Resistance Junction/Ambient		R_{thJA}	450K/W
Forward Current		I_F	100mA
Rise Time	$I_F=1.5A, t_p/T=0.01, t_p \leq 10\mu s$	T_r	400ns
Fall Time	$I_F=1.5A, t_p/T=0.01, t_p \leq 10\mu s$	T_f	450ns
Junction Temperature		T_j	100°C
Storage Temperature Range		T_{stg}	-25...+100°C
Radiant Intensity CQY 36N CQY 37N	$I_F=50mA, t_p \leq 20ns$	I_e	Min = 0.7mW/sr Typ = 1.5mW/sr Min = 2.2mW/sr

PHOTO

DETECTORS Silicon -NPN - Phototransistors

PARAMETER	CONDITIONS	SYMBOL	VALUE
Viewing Angle BPW 16N BPW 17N		φ	$\pm 40^\circ$
Peak Wavelength		λ_p	825nm
Thermal Resistance Junction/Ambient		R_{thJA}	450K/W
Forward Current		I_F	100mA
Rise Time	$V_s=5V, I_c=5mA, R_L=100\Omega$	T_r	4.8 μs
Fall Time	$V_s=5V, I_c=5mA, R_L=100\Omega$	T_f	5.0 μs
Junction Temperature		T_j	100°C
Storage Temperature Range		T_{stg}	-55...+100°C
Collector Light Current BPW 16N BPW 17N	$E_e=1mW/cm^2, \lambda=950nm, V_{ce}=5V$	I_{ca}	Min = 0.07mA Typ = 0.14mA Min = 0.5mA
Collector Emitter Voltage		V_{CEO}	32V
Collector Dark Current	$V_{CE} = 20V, E = 0$	I_{CEO}	Typ = 1nA

BEDFORD OPTO TECHNOLOGY LTD
1BIGGAR BUSINESS PARK, BIGGAR, LANARKSHIRE, ML12 6NR
Tel: +44 (0) 1899 221221 Fax: +44 (0) 1899 221009
Website: bot.co.uk E-mail: bill@bot.co.uk